

■ Mask ROMs

Process	Capacity	Configuration (words x bits)	* Pinout	Model No.	User's No.	Access time (ns) MAX. Cycle time (ns) MIN.	Supply current (mA) MAX.	Supply voltage (V)	Package	
CMOS	256k	32k x 8	J	LH53259D/N/T	LH5359XX	150	25	5 ± 10%	28DIP/28SOP/28TSOP(I) Forward bend	
	512k	64k x 8	J	LH53517D/N/T/TR	LH5317XX	150	30	5 ± 10%	28DIP/28SOP/28TSOP(II)	
	1M	128k x 8	J	LH531V00D/N/T/U	LH531VXX	100	75	5 ± 10%	32DIP/32SOP/32TSOP(II) Forward bend/32QFJ	
			J	LH53V1R00N/T	LH5V1RXX	120	30	2.7 to 3.6	32SOP/32TSOP(II) Forward bend	
			J	LH530800AD/AN/AU	LH531HXX	150	35	5 ± 10%	32DIP/32SOP/32QFJ	
			J	LH530800AD/AN-Y	LH531YXX	500*3 150*2	12*5	2.6 to 5.5	32DIP/32SOP	
			M	LH531000BD/BN	LH531GXX	150	35	5 ± 10%	28DIP/28SOP	
			M	LH531000BN-S	LH531MXX	500	18	2.6 to 3.6	28SOP	
			J	LH531024D/N/U	LH531CXX	100	75	5 ± 10%	40DIP/40SOP/44QFJ	
	2M	256k x 8	J	LH532100BD/BN/BT/BS/BSR/BU-1	LH532KXX	120	50	5 ± 10%	32DIP/32SOP/32TSOP(II) Forward bend/32TSOP(II)/32QFJ	
			J	LH532100BD/BN/BT/BS/BSR/BU	LH532KXX	150	50	5 ± 10%	32DIP/32SOP/32TSOP(II) Forward bend/32TSOP(II)/32QFJ	
		128k x 16	J	LH532048D/N/U	LH532CXX	100	75	5 ± 10%	40DIP/40SOP/44QFJ	
		256k x 8 128k x 16	M	LH532600D/N/T/TR	LH5326XX	100	75	5 ± 10%	40DIP/40SOP/48TSOP(II)	
			M	LH53V2P00N/T	LH5V2PXX	120	35	2.7 to 3.6	40SOP/48TSOP(II) Forward bend	
			M	LH532000BD/BN/BT/BTR-1	LH532GXX	120	50	5 ± 10%	40DIP/40SOP/48TSOP(II)	
			M	LH532000BD/BN/BT/BTR	LH532GXX	150	50	5 ± 10%	40DIP/40SOP/48TSOP(II)	
			M	LH532000BD/BN/BT/BTR-S	LH532SXX	500*3 150*2	15*5	2.6 to 5.5	40DIP/40SOP/48TSOP(II)	
			4M	512k x 8	J	LH53H4100D/N	LH5H41XX	80	90	5 ± 10%
		J			LH534700D/N	LH5S47XX	100	75	5 ± 10%	32DIP/32SOP
	J	LH534R00AD/AN/AS/ASR			LH5347XX	120	65	5 ± 10%	32DIP/32SOP/32TSOP(II)	
	F	LH534A00T			LH5S4AXX	120	65	5 ± 10%	32TSOP(I) Forward bend	
	F	LH534B00T			LH5S4BXX	120	60	5 ± 10%	40TSOP(II) Forward bend	
	256k x 16	J		LH534Y00D/U	LH534YXX	120	65	5 ± 10%	40DIP/44QFJ	
	512k x 8 256k x 16	M		LH53H4000D/N	LH5H40XX	80	90	5 ± 10%	40DIP/40SOP	
		M		LH534600BD/BN/BT/BTR	LH534VXX	100	75	5 ± 10%	40DIP/40SOP/48TSOP(II)	
		M		LH534P00AD/AN/AT/ATR	LH5348XX	120	65	5 ± 10%	40DIP/40SOP/48TSOP(II)	
		M		LH53B4P00D/N*1	LH5B4PXX	120[50]	100	5 ± 10%	40DIP/40SOP	
		M		★LH53V4P00N/T	LH5V4PXX	120	35	2.7 to 3.6	40SOP/48TSOP(II) Forward bend	
		M		LH534000BD/BN/BT-S	LH534SXX	500*3 200*2	15*5	2.6 to 5.5	40DIP/40SOP/48TSOP(II) Forward bend	
		8M		1M x 8	J	★LH538700AD/AN/AS	LH538VXX	100	100	5 ± 10%
	J		LH538R00BD/BN/BS/BSR		LH5387XX	120	60	5 ± 10%	32DIP/32SOP/32TSOP(II)	
	J		LH538300CD/CN/CS/CSR		LH538NXX	150	50	5 ± 10%	32DIP/32SOP/32TSOP(II)	

★ Under development

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CMOS	8M	1M x 8 512k x 16	M	LH53B8P00AD/AN*1	LH5B8GXX	120[50]	100	5 ± 10%	42DIP/44SOP		
			M	LH538600AD/AN/AT	LH538UXX	100	100	5 ± 10%	42DIP/44SOP/48TSOP(I) Forward bend		
			M	LH538P00BD/BN/BT/BTR	LH5388XX	120	60	5 ± 10%	42DIP/44SOP/48TSOP(I)		
			M	LH538500CD/CN/CT/CTR	LH538BXX	150	50	5 ± 10%	42DIP/44SOP/48TSOP(I)		
			M	LH53V8000D/N/T/TR	LH5V80XX	200*4 100*2	35*6	3.0 to 5.5	42DIP/44SOP/48TSOP(I)		
	16M	2M x 8 1M x 16	M	★LH53B16P00D/N*1	LH5B7PXX	120[50]	100	5 ± 10%	42DIP/44SOP		
			M	LH53C16P00D/N*1	LH5C7PXX	120[60]	150	5 ± 10%	42DIP/44SOP		
			M	LH53B16500D/N*1	LH5B75XX	150[70]	80	5 ± 10%	42DIP/44SOP		
			M	LH5316600D/N	LH5376XX	100	100	5 ± 10%	42DIP/44SOP		
			M	LH5316P00CD/CN	LH5372XX	120	70	5 ± 10%	42DIP/44SOP		
			M	LH5316P00CT/CTR	LH537DXX	120	70	5 ± 10%	48TSOP(I)		
			M	LH5316500CD/CN	LH5370XX	150	50	5 ± 10%	42DIP/44SOP		
			M	LH53V16500N/T	LH5V75XX	150	35	2.7 to 3.6	44SOP/48TSOP(I) Forward bend		
			M	LH53B16R00N *1	LH5B7RXX	120[50]	180	5 ± 10%	70SSOP		
			M	LH5324000D	LH5360XX	150	70	5 ± 10%	42DIP		
	24M	1.5M x 16	M	LH5324C00D	LH536CXX	120	80	5 ± 10%	42DIP		
			M	LH5324A00AD	LH536GXX	150	65	5 ± 10%	42DIP		
		3M x 8 1.5M x 16	M	LH5324P00N	LH536PXX	120	80	5 ± 10%	44SOP		
			M	★LH5324P00T/TR	LH536DXX	120	80	5 ± 10%	48TSOP(I)		
			M	LH5324500N	LH5365XX	150	70	5 ± 10%	44SOP		
			M	LH5332C00D	LH535CXX	120	80	5 ± 10%	42DIP		
	32M	2M x 16	M	LH5332A00D	LH535AXX	150	65	5 ± 10%	42DIP		
			M	LH5332600N	LH5356XX	100	100	5 ± 10%	44SOP		
		4M x 8 2M x 16	M	LH5332600T	LH535FXX	100	100	5 ± 10%	48TSOP(I) Forward bend		
			M	LH5332P00N	LH535PXX	120	80	5 ± 10%	44SOP		
			M	LH5332P00T/TR	LH535DXX	120	80	5 ± 10%	48TSOP(I)		
			M	LH5332500AN	LH535FXX	150	65	5 ± 10%	44SOP		
			M	LH53V32500N	LH5V55XX	150	35	2.7 to 3.6	44SOP		
			M	LH53V32500T/TR	LH5V5BXX	150	35	2.7 to 3.6	48TSOP(I)		
			64M	8M x 8 4M x 16	M	LH5364000N	LH5360XX	150	100	5 ± 10%	44SOP

⊕ : JEDEC standard EPROM pinout M : MASK ROM specific pinout F : Flash Memory compatible pinout

- *1 With Page mode. Figures in brackets indicate access time during page mode.
- *2 4.5 V ≤ Vcc ≤ 5.5 V
- *3 2.6 V ≤ Vcc < 4.5 V
- *4 3.0 V ≤ Vcc < 4.5 V
- *5 2.6 V ≤ Vcc ≤ 3.4 V
- *6 3.0 V ≤ Vcc ≤ 3.6 V

T : TSOP(Type I) Forward bend TR : TSOP(Type I) Reverse bend
 S : TSOP(Type II) Forward bend SR : TSOP(Type II) Reverse bend
 QFJ = PLCC